

## **Quarterly Reliability Monitoring Results**

## Quarters: Q1/2021 to Q4/2021

Based on structural similarity

| Supplier<br>Nexperia B.V. |   | User Part Number  |                                   |                  |            |           |  |  |
|---------------------------|---|---|-----------------------------------|------------------|------------|-----------|--|--|
|                           |   | BC856B  |                                   |                  |            |           |  |  |
| Name of Laboratory        |   | Part Description  |                                   |                  |            |           |  |  |
|                           |   | Nexperia DHAM   | Small Signal E                    | Bipolar Transist | or         |           |  |  |
| Assembly reliability labs |   | SMD package   |                                   |                  |            |           |  |  |
| Based on AEC-Q101 Test    |   | Test Conditions   | Duration                          | # Lots           | # Quantity | # Rejects |  |  |
|                           | TEST  |   |                                   |                  |            |           |  |  |
|                           | Pre- and Post-Stress                                    |   |                                   |                  |            |           |  |  |
| # E1                      | Electrical Test   | Tamb = 25 °C  | N/A                               | see below        | all parts  | see below |  |  |
| # A1                      | <b>PC</b> Preconditioning                               | JESD22-A113 Bake Tamb = 125 °C Soak Tamb = 85 °C, RH = 85% Reflow soldering                         | 24 hours<br>168 hours<br>3 cycles | 849              | 61170      | 0         |  |  |
| # B1                      | HTRB<br>High Temperature Reverse<br>Bias                | MIL-STD-750-1<br>M1039 Method A<br>Tj = Tjmax, Vr = 100% of max. datasheet<br>reverse voltage       | 1000 hours                        | 202              | 16160      | 0         |  |  |
| # A4                      | TC Temperature Cycling                                  | JESD22-A104<br>-65 °C to Tjmax, not to exceed 150°C   | 1000 cycles                       | 171              | 13680      | 0         |  |  |
| # A3 alt                  | <b>AC</b><br>Autoclave                                  | JESD22-A102<br>Tamb = 121 °C, RH = 100 %<br>Pressure = 205 kPa (29.7 psia)                          | 96 hours                          | 173              | 13840      | 0         |  |  |
| # A2 alt                  | H3TRB<br>High Humidity High<br>Temperature Reverse Bias | JESD22-A101 Tamb = 85 °C, RH = 85%, VR = 80 % of rated reverse voltage $^{[1]}$                     | 1000 hours                        | 173              | 13840      | 0         |  |  |
| # A5                      | <b>IOL</b><br>Intermittent Operating Life               | MIL-STD-750 Method 1037 ton = toff, devices powered to insure $\Delta Tj$ = 100 °C for 15000 cycles | 1000 hours                        | 197              | 15760      | 0         |  |  |
| # C8                      | <b>RSH</b><br>Resistance to Solder Heat                 | JESD22-A111<br>260 °C ± 5 °C  | 10 s                              | 135              | 4050       | 0         |  |  |
| # C10                     | <b>SD</b><br>Solderability                              | J-STD-002   |                                   | 342              | 3420       | 0         |  |  |

<sup>[1]</sup> The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

## **Calculation of FIT and MTTF**

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1)
Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

| Wafer Fab | Technology           | Quantity | Rejects | Failure Rate (FIT) | MTTF (hrs) |
|-----------|----------------------|----------|---------|--------------------|------------|
| Nexperia  | Small Signal Bipolar |          |         |                    |            |
| DHAM      | Transistor           | 16160    | 0       | 0.26               | 3.81E+09   |

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